

2N5457
2N5458
2N5459

**SILICON
N-CHANNEL JFETS**



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The CENTRAL SEMICONDUCTOR 2N5457, 2N5458, and 2N5459 are silicon N-Channel JFETs designed for switching and amplifier applications.



TO-92 CASE

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage	
Drain-Gate Voltage	
Gate-Source Voltage	
Continuous Gate Current	
Power Dissipation	
Operating and Storage Junction Temperature	

SYMBOL		UNITS
V_{DS}	25	V
V_{DG}	25	V
V_{GS}	25	V
I_G	10	mA
P_D	310	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

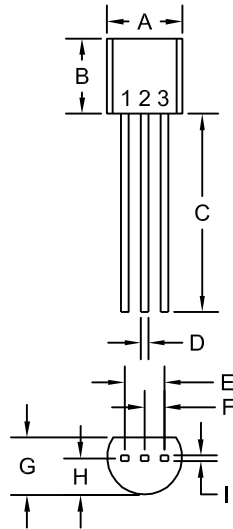
SYMBOL	TEST CONDITIONS	2N5457		2N5458		2N5459		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{GSS}	$V_{GS}=15\text{V}$	-	1.0	-	1.0	-	1.0	nA
I_{GSS}	$V_{GS}=15\text{V}, T_A=100^\circ\text{C}$	-	200	-	200	-	200	nA
I_{DSS}	$V_{DS}=15\text{V}$	1.0	5.0	2.0	9.0	4.0	16	mA
BV_{GSS}	$I_G=10\mu\text{A}$	25	-	25	-	25	-	V
$V_{GS(OFF)}$	$V_{DS}=15\text{V}, I_D=10\text{nA}$	0.5	6.0	1.0	7.0	2.0	8.0	V
C_{rss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$	-	3.0	-	3.0	-	3.0	pF
C_{iss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$	-	7.0	-	7.0	-	7.0	pF
g_{fs}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{kHz}$	1.0K	5.0K	1.5K	5.5K	2.0K	6.0K	μS
g_{os}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{kHz}$	-	50	-	50	-	50	μS

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TO-92 CASE - MECHANICAL OUTLINE



R1

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

LEAD CODE:

- 1) Drain
- 2) Source
- 3) Gate

MARKING:

FULL PART NUMBER

R1 (6-March 2014)